

1. Scope :

This specification applies to InGaAs PIN photodiode chips.
Device No. ED-MPD25VB

2. Structure :

- 2-1. Type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Au alloy.
Back side (Cathode) : Au alloy.

3. Size :

- 3-1. Chip size : 24.7 mils × 24.7 mils (0.628 mm × 0.628 mm).
3-2. Chip thickness : 7.9 ± 1 mils (0.20 ± 0.025 mm).
3-3. Aperture size : 19.7 mils × 19.7 mils (0.50 mm × 0.50 mm).
3-4. Bonding pad (Anode) : 3.9 × 3.9 mils (0.100 mm × 0.100mm).
3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse Dark Current	I_D	$V_R=5V$ $E_e=0mW/cm^2$	-	-	1	nA
*Reverse Breakdown Voltage	V_R	$I_R=1\mu A$ $E_e=0mW/cm^2$	30	-	-	V
*Forward Voltage	V_F	$I_F=3mA$ $E_e=0mW/cm^2$	-	-	0.7	V
Capacitance	C_p	$V_R=5V$ $f=1MHz$	-	-	20	pF
Responsivity	Resp	$V_R=5V$ Wavelength =1310nm	0.8	-	-	A/W

*Based on 100% probing

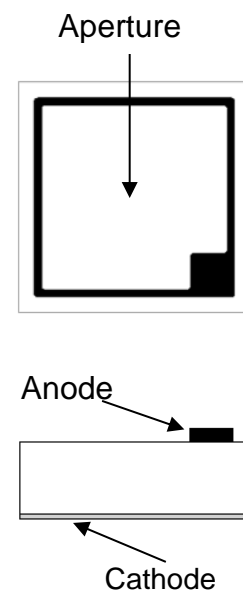
**5. Typical Electro-Optical Characteristics Curve:**

Fig 1. Relative Responsivity vs Wavelength

